	'6 RQ0$;5	,'
9	P # 9	$
	P # 9	
	P # 9	

026)(7 ((/(&75,&$/ &+$5$&7(5,67,&6 QOHVV RWKHUZLVH VSHFLILHG

3DUDPHWHU	6\PERO	7HVW &RQGLWLRQ	0LQ	7\S	0D[	8QLW
2II FKDUDFWHULVWLFV						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250 A	20			V
Gate-body leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±1 V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS}=20V, V_{GS} =0V			1.0	A
2Q FKDUDFWHULVWLFV						
Gate-threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =0.25mA	0.70		1.50	V
Static drain-source on-resistance (note 1)	$R_{DS(on)}$	V_{GS} =10V, I_D =4A			0.038	Ÿ
		V_{GS} =4.5V, I_D =4A			0.05	
		V_{GS} =2.5V, I_D =3A			0.08	
Forward transconductance (note 1)	g_{fs}	V_{DS} =5V, I_D =3A	3			S
'\QDPLF FKDUDFWHULVWLFV QRWH						
Input capacitance	C_{iss}	V_{DS} =20V,V_{GS} =0V, f=1MHz			570	pF
Output capacitance	C_{oss}			80		
Reverse transfer capacitance	C_{rss}			65		
6ZLWFKLQJ FKDUDFWHULVWLFV						
Turn-on delay time (note 1,2)	$t_{d(on)}$	V_{GS}=5V, V_{DS}=10V, I_D =1A,R_{GEN}=3.3 , R_D=10		8		ns
Rise time (note 2)	t_r			9		
Turn-off delay time (note 2)	$t_{d(off)}$			13		
Fall time (note 2)	t_f			3		
'UDLQ VRXUFH ERG\ GLRGH FKDUDFWHULVWLFV						
Body diode forward voltage (note 1)	V_{SD}	I_S=1A, V_{GS} = 0V			1.3	V

1RWHV

1. Pulse Test ; Pulse Width ”300 s, Duty Cycle ”2%.

2. These parameters have no way to verify.